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Author Yi Chang Chen
Author's Email Address No Public.
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Abstract
This dissertation is about " The Lithography process flow, include Coating, Exposure, Developer, Baking Processing etc. We will introduce the Defect types, root cause, how to classification. And we will use some experiment methods to prevent that Defect count to increase. Example the exhaust press change, recipe & hardware modify, temperature & time re-setting etc.
The other, The photo lithography steps affecting CD uniformity include Coating, Baking, Exposure and Developing. Especially, the Developing step would be the critical factor affecting CD uniformity. Therefore, there is a need to study key parameters in Developing step which Nozzle Scan Speed, Gap, Flow rate and Tilt. Besides good CD uniformity, low defect level of those parameters are required especially free from critical defect types. Through the investigation of this study, good CD performances and low defect level can be achieved which allowed setting better production specification and increase production yield.
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